



Guerrilla RF Expands GaN Design Support and Begins Sampling New High-Power Devices

New GRF0005 and GRF0012 nonlinear models added to Modelithics COMPLETE Library™; GRF0051, GRF0110 and GRF0150 now sampling for tactical radio, UAS and C-UAS applications

GREENSBORO, NC — October 20, 2026 — Guerrilla RF, Inc. (OTCQX: GUER), a leading provider of high-performance RF and microwave semiconductors, today announced that new nonlinear simulation models for its **GRF0005** and **GRF0012** gallium nitride (GaN) power transistors are now available in the Modelithics COMPLETE Library™. The Company also announced that it is sampling three new high-power GaN-on-Silicon Carbide (GaN-on-SiC) devices targeting both commercial and Aerospace & Defense markets. In particular, the broadband nature of these devices makes them ideal for **Tactical Radio**, **UAS (Drone)**, and **C-UAS (counter drone)** applications.

Modelithics provides measurement-based RF and microwave simulation models that engineers use in electronic design automation software to assess component performance before building hardware. The new **GRF0005** and **GRF0012** models extend design support across Guerrilla RF's GaN portfolio from 5 W to 150 W.

"Making these models available through the Modelithics COMPLETE Library™ is an important step in expanding Guerrilla RF's GaN platform," said Ryan Pratt, Founder and CEO of Guerrilla RF. "It gives customers a more practical way to evaluate performance early in the design process and move toward production with greater confidence. Our growing portfolio of GaN models continues to build on our RF design expertise and expands our ability to serve higher-power applications across military systems and wireless infrastructure, which are among the Company's fastest-growing segments. As these programs advance, we expect revenue derived from our GaN portfolio to ramp through 2027 and beyond, positioning the platform to become a meaningful growth driver for Guerrilla RF."

The **GRF0005** and **GRF0012** are 5 W and 12 W devices, respectively, with both operating from DC to 12 GHz. These transistor cores natively support 40 V operation and are also compatible with 28 V supply rails. Together with the six GaN models announced earlier this year, the two new models broaden customer access to simulation tools that support design-in activity, shorten development cycles and advance adoption of Guerrilla RF's high-power GaN portfolio. To learn more about Guerrilla RF's entire GaN offering, visit guerrilla-rf.com/GaN.

Model Capabilities

Nonlinear models are designed to show how a transistor performs under the higher-power operating conditions used in RF amplifiers. The models help engineers assess tradeoffs involving power, efficiency, linearity and thermal performance before committing to hardware.

- **Large-signal behavior:** Evaluates output power, compression, distortion and efficiency.
- **Bias and thermal effects:** Assesses changes in operating conditions, including self-heating.
- **Load-pull analysis:** Helps identify source and load impedances that support power, efficiency and linearity objectives.

The **GRF0005** and **GRF0012** models are available now through the Modelithics COMPLETE Library™. To learn more or request access, visit modelithics.com/mvp/guerrillarf.

Product Development Update

Guerrilla RF is now sampling three additional discrete GaN-on-SiC high-electron-mobility transistors (HEMTs) for both commercial and Aerospace & Defense applications:

- **GRF0051**: 50 W P3dB, DC to 6 GHz, supporting 28 V and 50 V operation.
- **GRF0110**: 110 W P3dB, DC to 3.7 GHz, supporting 28 V and 50 V operation.
- **GRF0150**: 150 W P3dB, DC to 3.2 GHz, supporting 28 V and 50 V operation.

The devices are expected to move into full production in the near term. Together, they extend Guerrilla RF's high-power GaN roadmap for applications like **Tactical Radio**, **UAS (Drone)**, and **C-UAS (counter drone)** systems where broadband performance, thermal capability and design flexibility are important.

The expanded model library and continued product sampling are intended to support customer design activity and accelerate commercialization of Guerrilla RF's high-power GaN portfolio. For more information on Guerrilla RF's GaN portfolio, including available products and design resources, visit guerrilla-rf.com/GaN.

About Guerrilla RF

Founded in 2013, Guerrilla RF, Inc., develops and manufactures high-performance, state-of-the-art radio frequency (RF) and microwave semiconductors for wireless OEMs in multiple high-growth market segments, including network infrastructure for 5G/4G macro and small cell base stations, SATCOM, cellular repeaters/DAS, automotive telematics, military communications, navigation, and high-fidelity wireless audio. The Company has an extensive portfolio of 194 high-performance RF and microwave semiconductor devices. As one of the fastest-growing semiconductor firms in the industry, Guerrilla RF drives innovation through its R&D to commercialization initiatives and focuses on product excellence and custom solutions to underserved markets. The Company has shipped over 330 million devices. For more information, please visit <https://www.guerrilla-rf.com/> or follow the Company on [Twitter](#) and [LinkedIn](#).

Forward-Looking Statements

This press release may contain forward-looking statements within the meaning of Section 21E of the Securities Exchange Act of 1934 and the Private Securities Litigation Reform Act of 1995, which statements are inherently subject to risks and uncertainties. Forward-looking statements include projections, predictions, expectations, or beliefs about future events or results or otherwise are not statements of historical fact. Such statements are often characterized by the use of qualifying words (and their derivatives) such as "expect," "believe," "estimate," "plan," "project," "anticipate," or other statements concerning opinions or judgments of the Company and its management about future events. You should not place undue reliance on forward-looking statements because they involve known and unknown risks, uncertainties, and assumptions that are difficult or impossible to predict and, in some cases, beyond the Company's control. Actual results may differ materially from those in the forward-looking statements as a result of several factors, including those described in the Company's filings with the SEC available at <https://www.sec.gov>. Forward-looking statements speak only as of the date they are made. The Company undertakes no obligation to revise or update information in this release to reflect events or circumstances in the future, even if new information becomes available.

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